



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

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MMBT918LT1G

VHF/UHF Transistor

NPN Silicon

Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--------------------------------|-----------|-------|------|
| Collector–Emitter Voltage | V_{CEO} | 15 | Vdc |
| Collector–Base Voltage | V_{CBO} | 30 | Vdc |
| Emitter–Base Voltage | V_{EBO} | 3.0 | Vdc |
| Collector Current – Continuous | I_C | 50 | mAdc |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|-----------------|-------------|----------------------------|
| Total Device Dissipation FR–5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D | 225 1.8 | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction–to–Ambient | $R_{\theta JA}$ | 556 | $^\circ\text{C}/\text{W}$ |
| Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D | 300 2.4 | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction–to–Ambient | $R_{\theta JA}$ | 417 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature | T_J, T_{stg} | –55 to +150 | $^\circ\text{C}$ |

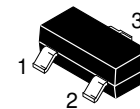
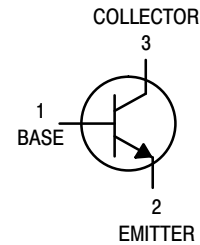
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR–5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



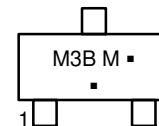
ON Semiconductor®

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SOT–23 (TO–236)
CASE 318
STYLE 6

MARKING DIAGRAM



M3B = Device Code
M = Date Code*
■ = Pb–Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

| Device | Package | Shipping† |
|-------------|---------------------|--------------------|
| MMBT918LT1G | SOT–23 (Pb–Free) | 3000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBT918LT1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|---|---------------|--------|------------|------|
| OFF CHARACTERISTICS | | | | |
| Collector–Emitter Breakdown Voltage ($I_C = 3.0\text{ mA}$, $I_B = 0$) | $V_{(BR)CEO}$ | 15 | – | Vdc |
| Collector–Base Breakdown Voltage ($I_C = 1.0\text{ }\mu\text{A}$, $I_E = 0$) | $V_{(BR)CBO}$ | 30 | – | Vdc |
| Emitter–Base Breakdown Voltage ($I_E = 10\text{ }\mu\text{A}$, $I_C = 0$) | $V_{(BR)EBO}$ | 3.0 | – | Vdc |
| Collector Cutoff Current ($V_{CB} = 15\text{ Vdc}$, $I_E = 0$) | I_{CBO} | – | 50 | nAdc |
| ON CHARACTERISTICS | | | | |
| DC Current Gain ($I_C = 3.0\text{ mA}$, $V_{CE} = 1.0\text{ Vdc}$) | h_{FE} | 20 | – | – |
| Collector–Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 1.0\text{ mA}$) | $V_{CE(sat)}$ | – | 0.4 | Vdc |
| Base–Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 1.0\text{ mA}$) | $V_{BE(sat)}$ | – | 1.0 | Vdc |
| SMALL–SIGNAL CHARACTERISTICS | | | | |
| Current–Gain – Bandwidth Product ($I_C = 4.0\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f = 100\text{ MHz}$) | f_T | 600 | – | MHz |
| Output Capacitance ($V_{CB} = 0\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$) ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$) | C_{obo} | – – | 3.0 1.7 | pF |
| Input Capacitance ($V_{EB} = 0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$) | C_{ibo} | – | 2.0 | pF |
| Noise Figure ($I_C = 1.0\text{ mA}$, $V_{CE} = 6.0\text{ Vdc}$, $R_S = 50\text{ }\Omega$, $f = 60\text{ MHz}$) (Figure 1) | NF | – | 6.0 | dB |
| Power Output ($I_C = 8.0\text{ mA}$, $V_{CB} = 15\text{ Vdc}$, $f = 500\text{ MHz}$) | P_{out} | 30 | – | mW |
| Common–Emitter Amplifier Power Gain ($I_C = 6.0\text{ mA}$, $V_{CB} = 12\text{ Vdc}$, $f = 200\text{ MHz}$) | G_{pe} | 11 | – | dB |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

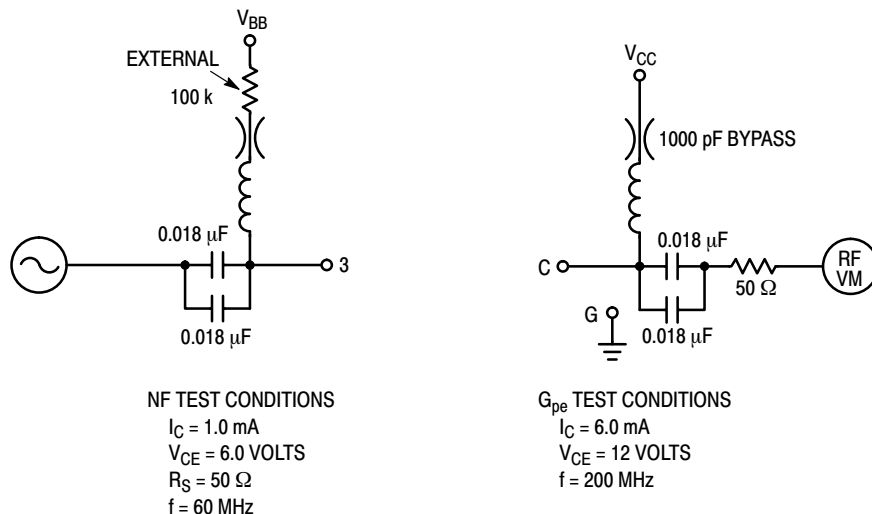
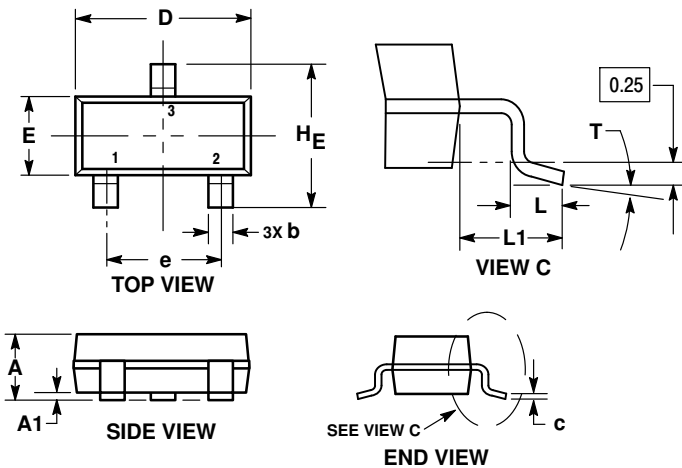


Figure 1. NF, G_{pe} Measurement Circuit 20–200

MMBT918LT1G

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AR



NOTES:

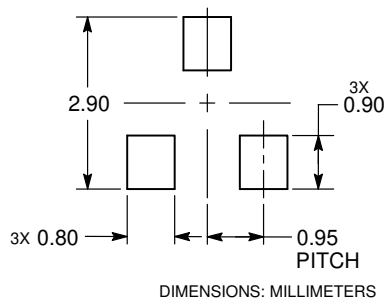
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| DIM | MILLIMETERS | | | INCHES | | |
|-----|-------------|------|------|--------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.89 | 1.00 | 1.11 | 0.035 | 0.039 | 0.044 |
| A1 | 0.01 | 0.06 | 0.10 | 0.000 | 0.002 | 0.004 |
| b | 0.37 | 0.44 | 0.50 | 0.015 | 0.017 | 0.020 |
| c | 0.08 | 0.14 | 0.20 | 0.003 | 0.006 | 0.008 |
| D | 2.80 | 2.90 | 3.04 | 0.110 | 0.114 | 0.120 |
| E | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| e | 1.78 | 1.90 | 2.04 | 0.070 | 0.075 | 0.080 |
| L | 0.30 | 0.43 | 0.55 | 0.012 | 0.017 | 0.022 |
| L1 | 0.35 | 0.54 | 0.69 | 0.014 | 0.021 | 0.027 |
| HE | 2.10 | 2.40 | 2.64 | 0.083 | 0.094 | 0.104 |
| T | 0° | --- | 10° | 0° | --- | 10° |

STYLE 6:

- PIN 1. BASE
- EMITTER
- COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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